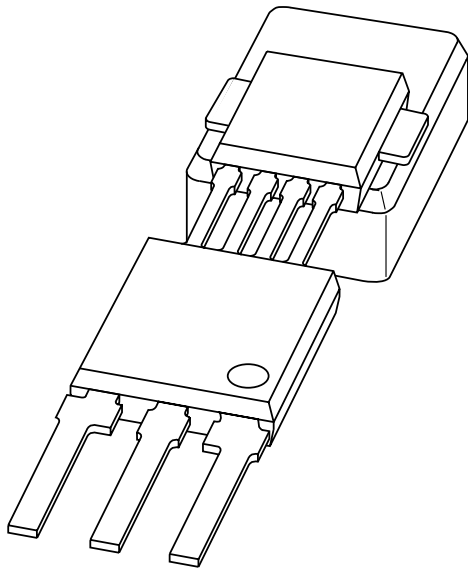


DATA SHEET



KMI18/4 Integrated rotational speed sensor

Objective specification

2000 Sep 05

Integrated rotational speed sensor

KMI18/4

FEATURES

- Open collector output
- For active target wheel application
- Wide air gap
- Zero speed capability
- Wide temperature range
- Insensitive to vibration.

DESCRIPTION

The KMI18/4 sensor detects rotational speed of passive targets wheels with ferrous reference marks.

It consists of a magnetoresistive sensor element, an integrated circuit for signal conditioning and a ferrite magnet.

The frequency of the digital voltage output signal is proportional to the rotational speed of the target wheel (see Fig.3).

An open collector output gives high flexibility in the design of the subsequent signal conditioning.

CAUTION
Do not press two or more products together against their magnetic forces. Do not expose products to strong magnetic fields of more than 30 kA/m.

PINNING

PIN	SYMBOL	DESCRIPTION
1	V _{CC}	DC supply
2	OUT	open collector output
3	GND	ground

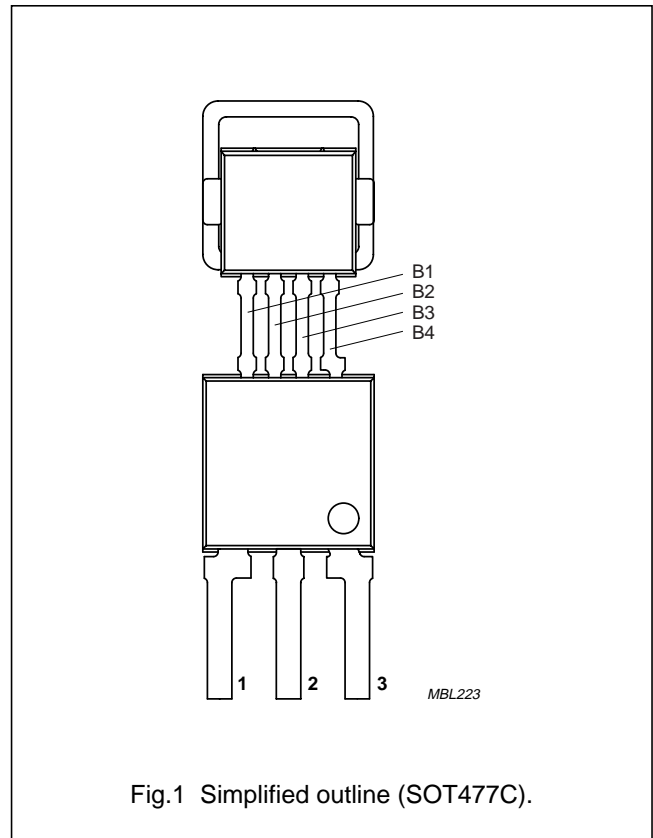


Fig.1 Simplified outline (SOT477C).

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{CC}	DC supply voltage	T _{amb} = -40 to +150 °C	4.5	5	16.5	V
I _{CC}	DC supply current	V _{CC} = 5 V	6	7	10	mA
d _{max}	maximum sensing distance	gear wheel; see Fig.4	2.2	2.7	–	mm
d _{min}	minimum sensing distance	gear wheel; see Fig.4	–	–	0.3	mm
T _{amb}	ambient operating temperature	V _{CC} = 5 V; note 1	-40	–	+150	°C

Note

1. Maximum power consumption according to power derating curve, see Fig.5.

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LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 60134) for $T_{amb} = -40$ to $+150$ °C; see Fig.6.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CC}	DC supply voltage	not protected against incorrect polarity	-0.5	+16.5	V
V_{OUT}	output voltage	not protected against incorrect polarity	-0.5	+24	V
$I_{OUT(max)}$	maximum output current	low state; note 1	-	20	mA
$I_{OUT(high)}$	output leakage current	high state; note 2; see Fig.7	-	100	μ A
		high state; note 2; see Fig.8	-	100	μ A
P_{tot}	total power dissipation	$V_{CC} = 16.5$ V; $I_{OUT} = 20$ mA	-	300	mW
T_{amb}	ambient operating temperature	$V_{CC} = 5$ V	-40	+150	°C
T_{stg}	storage temperature		-40	+150	°C
T_{sld}	soldering temperature	$t \leq 10$ s	-	260	°C

Notes

1. LOW: open collector output transistor open ($V_{OUT} < 1$ V).
2. HIGH: open collector output transistor closed ($V_{OUT} > 4$ V).

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CHARACTERISTICS

$T_{amb} = 26 \pm 10 \text{ }^\circ\text{C}$; $V_{CC} = 5 \text{ V}$; $f_{rm} = 0$ to 25000 Hz; gear wheel according to Fig.4; magnetic reading point Fig.10 unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Sensor characteristics						
d_{max}	maximum sensing distance	$T_{amb} = -40$ to $+150 \text{ }^\circ\text{C}$	2.2	2.7	–	mm
d_{min}	minimum sensing distance	$T_{amb} = -40$ to $+150 \text{ }^\circ\text{C}$	–	–	0.3	mm
$\Delta\phi$	repeatability of rotational angle	T_{amb} ; f_{rm} ; d ; = constant	–	0.01	0.02	deg
H_{yLH}	magnetic trigger field strength (threshold) for LH-output edge	$T_{amb} = -40$ to $+150 \text{ }^\circ\text{C}$	–200	+300	+600	A/m
H_{yHL}	magnetic trigger field strength (threshold) for HL-output edge	$T_{amb} = -40$ to $+150 \text{ }^\circ\text{C}$	–600	–300	+200	A/m
H_{y0}	magnetic offset		–200	–	+200	A/m
H_{yh}	magnetic trigger hysteresis		100	500	700	A/m
H_x	auxiliary magnetic field strength		–11	–5.8	–3	kA/m
f_{rm}	frequency of magnetic reference marks		0	–	25000	Hz
Supply conditions						
I_{CC}	DC supply current	$T_{amb} = 26 \pm 10 \text{ }^\circ\text{C}$; $V_{CC} = 5 \text{ V}$	6.5	7.5	8.5	mA
		$T_{amb} = -40$ to $+150 \text{ }^\circ\text{C}$; $V_{CC} = 5 \text{ V}$	6	7	10	mA
V_{CC}	DC supply voltage	$T_{amb} = -40$ to $+150 \text{ }^\circ\text{C}$;	4.5	5	16.5	V
Signal output characteristics						
	transfer behaviour	change of position of reference mark	see Fig.3			
	power-on state		undefined			
I_{OUT}	output current	low state; note 1	0.1	–	20	mA
$I_{OUT(high)}$	output leakage current	high state; note 2; see Fig.7	–	–	100	μA
V_{OUT}	output saturation voltage	$T_{amb} = -40$ to $150 \text{ }^\circ\text{C}$; low state; note 1 $I_{OUT} = 1 \text{ mA}$	0.01	0.03	0.1	V
		$I_{OUT} = 10 \text{ mA}$	0.1	0.2	0.5	V
		$I_{OUT} = 20 \text{ mA}$	0.3	0.5	1	V
t_{rOUT}	output signal rise time	low 10% to high 90%; see Fig.9	5	12	20	μs
t_{fOUT}	output signal fall time	high 90% to low 10%; see Fig.9	0.05	0.5	1	μs

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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
t_{drOUT}	output signal delay time of HL-edge		1.95	2.3	2.55	μs
		$T_{\text{amb}} = (-40 \text{ to } +150) \text{ }^\circ\text{C}$	1.5	–	3.5	μs
d_{drfOUT}	jitter of HL-edge	normalized to cycle of one reference mark; note 3	0	–	0.15	%
Environmental conditions						
	external magnetic influence	note 4	–	–	30	kA/m
	ESD protection of sensor pins V_{CC} , OUT and GND	compliance to IEC 0801-2 (IV); note 5	2	–	–	kV
	ESD protection of internal pins B1, B2, B3 and B4	compliance to IEC 0801-2 (IV); note 6	0.3	–	–	kV
	EMC: Compliance to ISO 11452-5	(A, stripline, 300 V/m, 10 kHz to 400 MHz, 1500 mm); note 7	–	–	–	
	interference for pulse: ISO 7637; pulse 4	$T = 25 \text{ }^\circ\text{C}$; note 7	function A			
Capacity of sensor shield						
C_s	shield capacity	B1 versus B2 of MR bridge; $f = 1 \text{ MHz}$; $U_{\text{osc}} = 200 \text{ mV}$	37	43	48	pF

Notes

1. LOW: open collector output transistor open ($V_{\text{OUT}} < 1 \text{ V}$).
2. HIGH: open collector output transistor closed ($V_{\text{OUT}} > 4 \text{ V}$).
3. Measured with harmonic magnetic field in 'y' with $H_{y \text{ max}} = 1 \text{ kA/m}$ and $f_m = 10, 1000 \text{ and } 8000 \text{ Hz}$.
4. Higher magnetic fields could cause irreversible shifts of parameters.
5. Output pins are designed for electrostatic sensitivity with field strengths up to 2 kV according to Human Body Model (HBM), MIL-STD-883, Method 3015.
6. MR pins are designed for electrostatic sensitivity with field strengths up to 0.3 kV according to Human Body Model (HBM), MIL-STD-883, Method 3015.
7. Measured with harmonic magnetic field in 'y' with $H_{y \text{ max}} = 1 \text{ kA/m}$ and $f_m = 50 \text{ Hz}$.

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FUNCTIONAL DESCRIPTION

The KMI18/4 is sensitive to the rotation of an passive target wheel with ferrous reference marks. The functional principle is shown in Fig.3. Because of the sensor layout and setup of the measuring system, only movements of reference marks in the y-direction will be sensed (coordinate system see Fig.2).

The electrical output signal of the sensor is amplified, temperature compensated and applied to a Schmitt trigger in the signal conditioning circuit (see Fig.11). An additional housing separates the conditioning circuitry from the magnetoresistive sensor element, thereby ensuring optimal sensor performance at high temperatures.

The signal level of the digital output is independent from the sensing distance within the measuring range. Its frequency equals that of the reference marks on the target wheels. Accuracy of the HL-edge, as a measure of the rotational angle, strongly depends on the properties of the chosen target wheel and the operating conditions.

An open collector voltage interface ensures accurate transmission (three wires) of the digital sensor signal to the subsequent signal conditioning electronics.

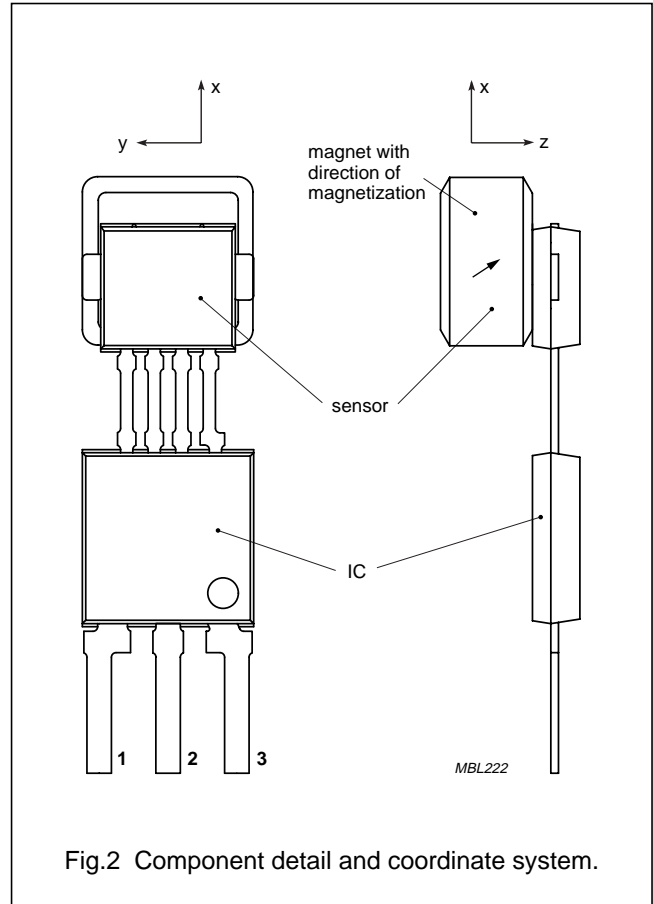


Fig.2 Component detail and coordinate system.

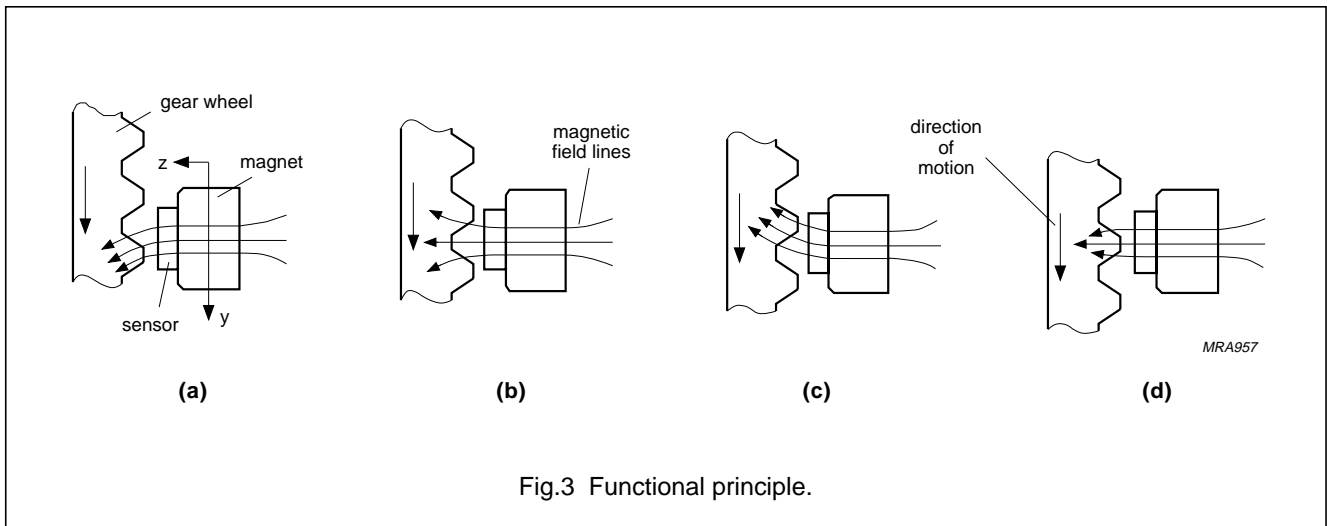


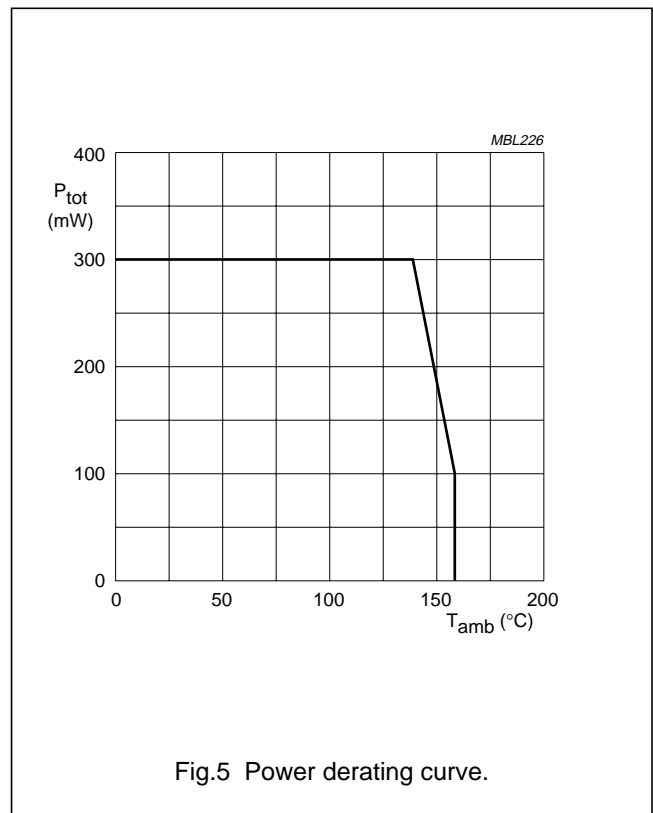
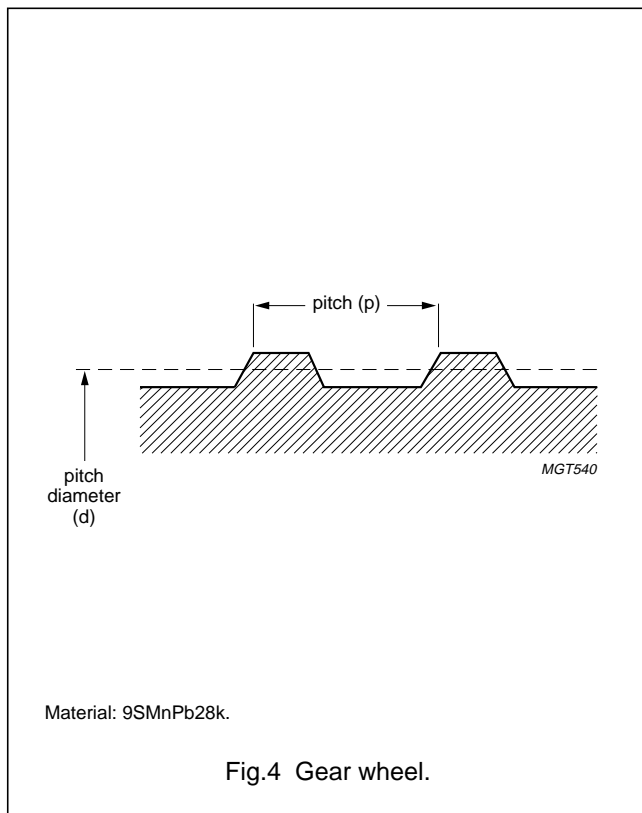
Fig.3 Functional principle.

Integrated rotational speed sensor

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Table 1 Gear wheel dimensions

SYMBOL	DESCRIPTION	VALUE	UNIT
German DIN			
z	number of teeth	50	
d	diameter	104	mm
m	module $m = d/z$	2.08	mm
p	pitch $\pi = p \times m$	6.53	mm
ASA			
PD	pitch diameter (d in inches)	4.09	inch
DP	diametric pitch $DP = 25.4 \text{ mm/m}$	12.2	inch ⁻¹
CP	circular pitch $CP = p/25.4 \text{ mm}$	0.26	inch



Integrated rotational speed sensor

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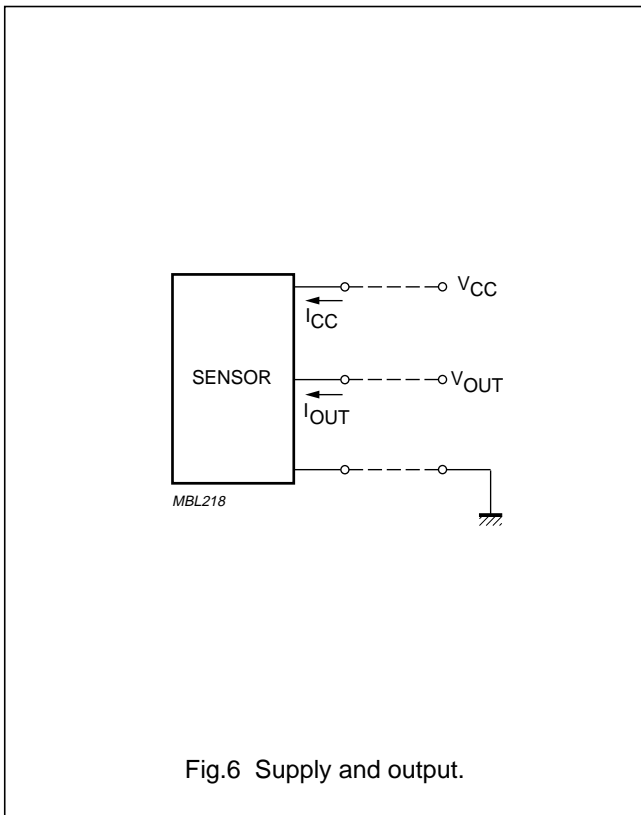


Fig.6 Supply and output.

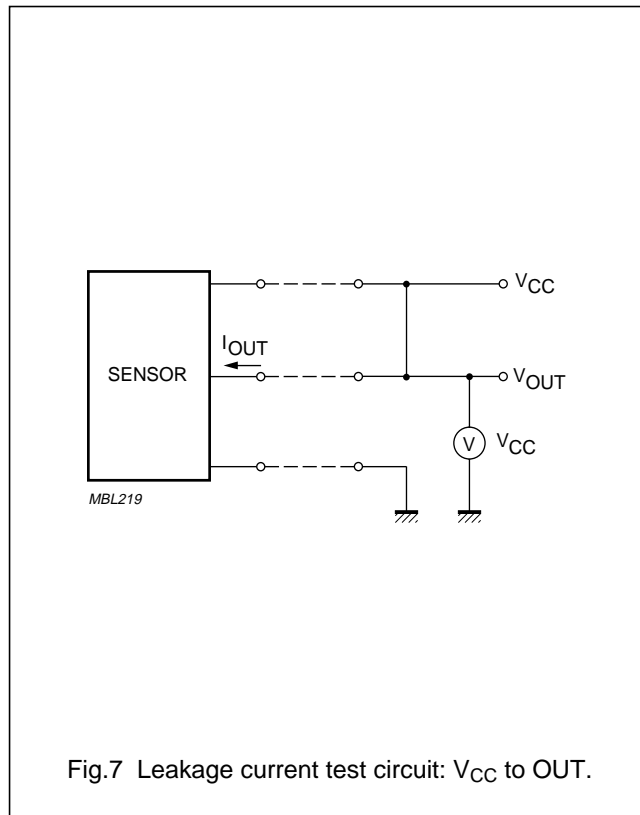


Fig.7 Leakage current test circuit: V_{CC} to OUT.

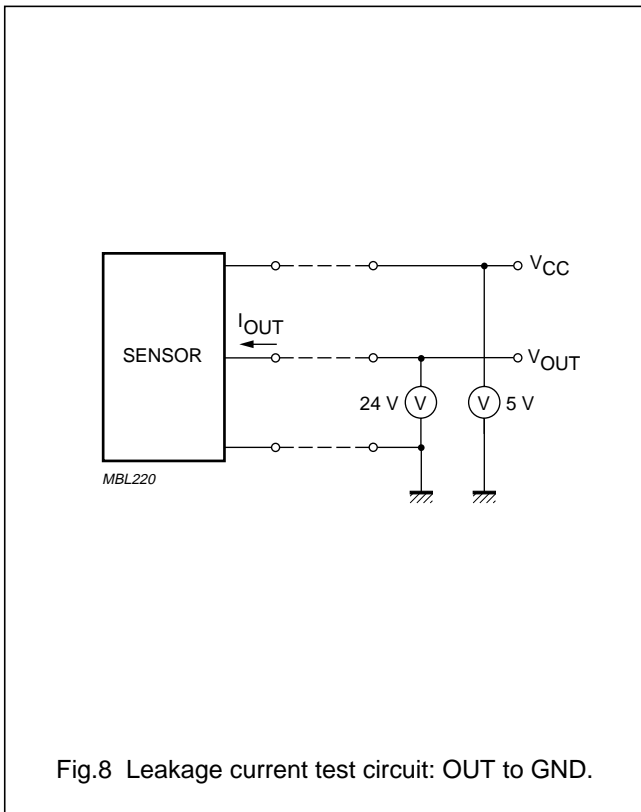


Fig.8 Leakage current test circuit: OUT to GND.

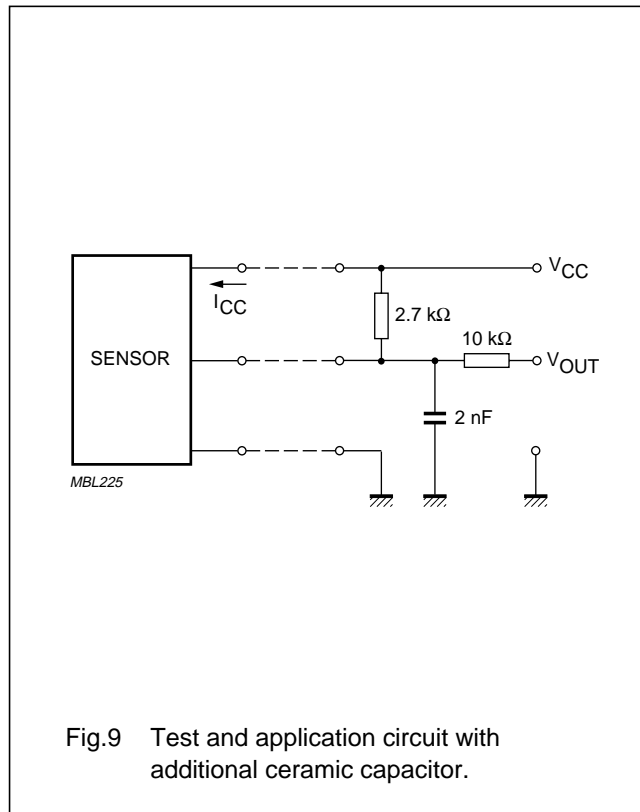
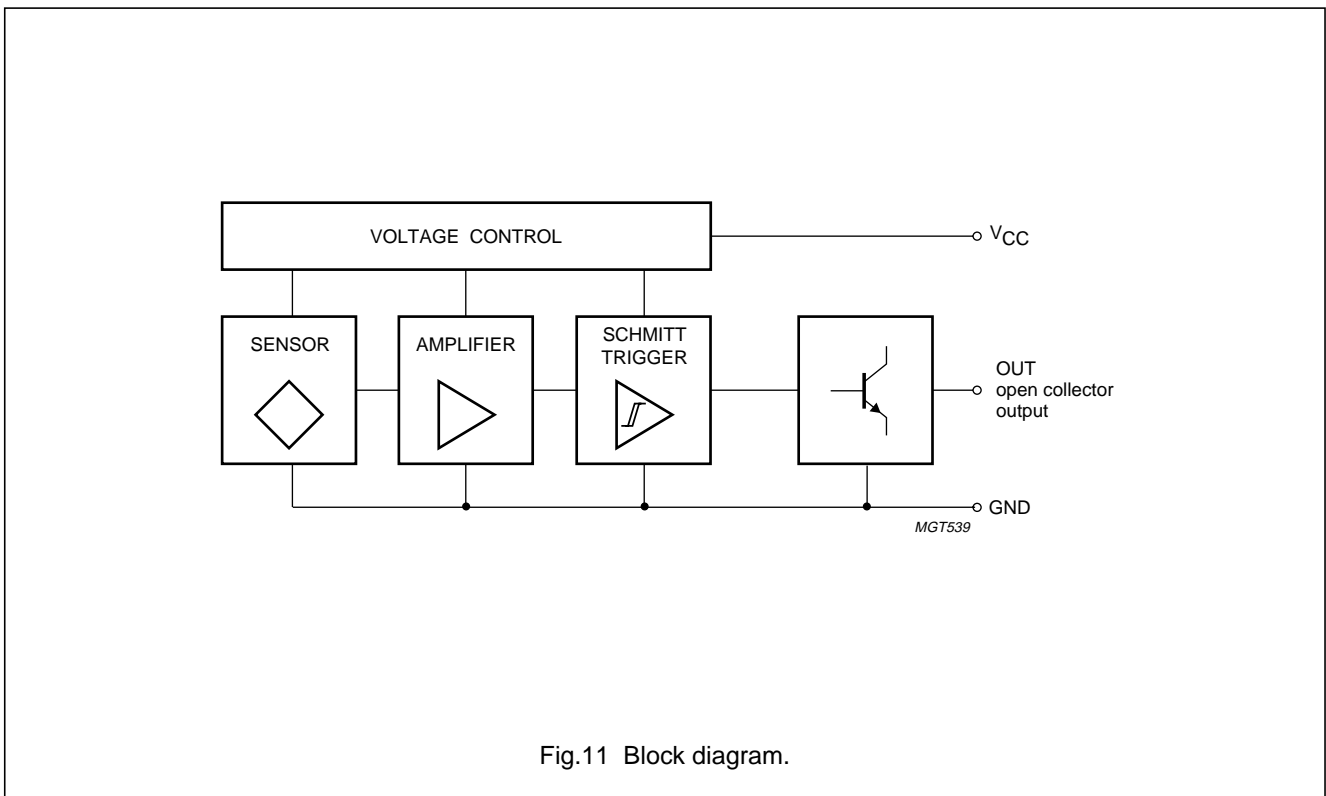
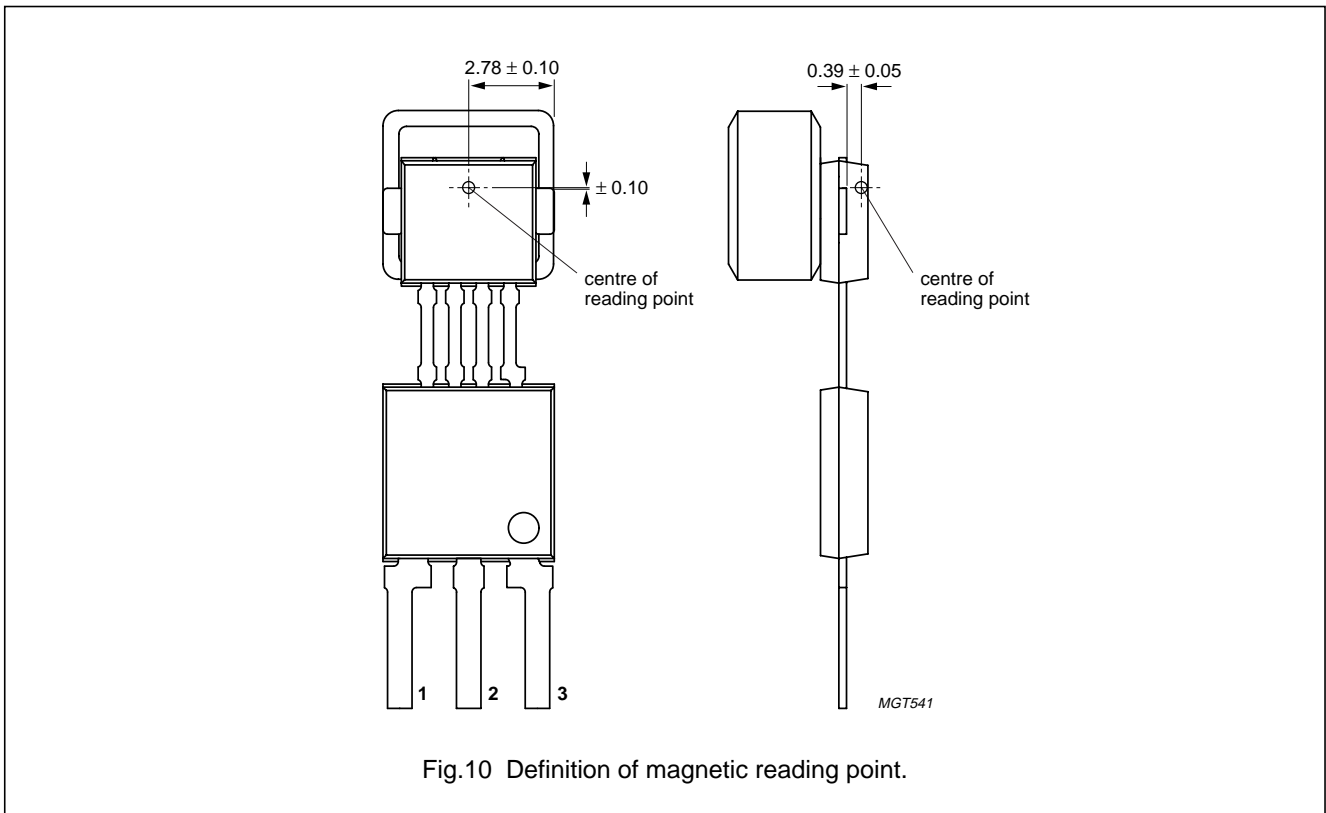


Fig.9 Test and application circuit with additional ceramic capacitor.

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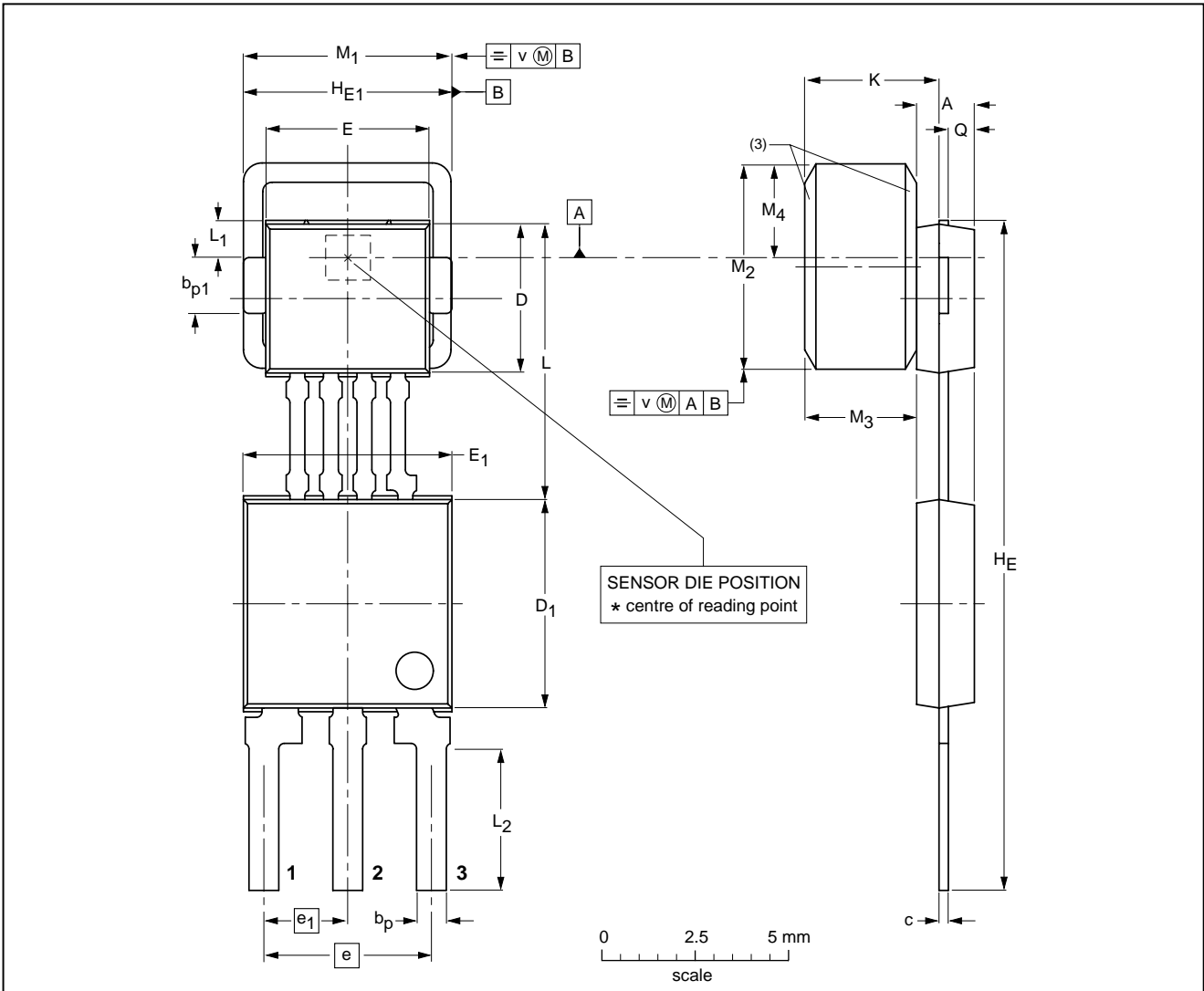
Integrated rotational speed sensor

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PACKAGE OUTLINE

Plastic single-ended multi-chip package;
magnetized ferrite magnet (5.5 x 5.5 x 3 mm); 4 interconnections; 3 in-line leads

SOT477C



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾	b _p	b _{p1}	c	D ⁽²⁾	D ₁ ⁽²⁾	E ⁽²⁾	E ₁ ⁽²⁾	e	e ₁	H _E	H _{E1}	K _{max.}	L	L ₁	L ₂	M ₁	M ₂	M ₃ ⁽¹⁾	M ₄	Q	v
mm	1.7	0.8	1.57	0.3	4.1	5.7	4.5	5.7	4.6	2.35	18.2	5.6	3.87	7.55	1.2	3.9	5.65	5.65	3.05	2.6	0.75	0.25
	1.4	0.7	1.47	0.24	3.9	5.5	4.3	5.5	4.4	2.15	17.8	5.5		7.25	0.9	3.5	5.35	5.35	2.95	2.4	0.65	

Notes

1. Glue thickness not included.
2. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
3. Magnet chamber optional.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT477C						00-08-31

Integrated rotational speed sensor

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DATA SHEET STATUS

DATA SHEET STATUS	PRODUCT STATUS	DEFINITIONS ⁽¹⁾
Objective specification	Development	This data sheet contains the design target or goal specifications for product development. Specification may change in any manner without notice.
Preliminary specification	Qualification	This data sheet contains preliminary data, and supplementary data will be published at a later date. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.
Product specification	Production	This data sheet contains final specifications. Philips Semiconductors reserves the right to make changes at any time without notice in order to improve design and supply the best possible product.

Note

1. Please consult the most recently issued data sheet before initiating or completing a design.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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